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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/519,672	03/06/2000	Toshihiko Ouchi	35.G2544	8718

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EXAMINER

THOMAS, COURTNEY D

ART UNIT

PAPER NUMBER

2882

DATE MAILED: 05/22/2003

Please find below and/or attached an Office communication concerning this application or proceeding.



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APPLICATION NO./ CONTROL NO.	FILING DATE	FIRST NAMED INVENTOR / PATENT IN REEXAMINATION	ATTORNEY DOCKET NO.
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EXAMINER

ART UNIT PAPER

13

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Commissioner of Patents and Trademarks

The following represents the corrected heading regarding the examiner's treatment of claims 86 and 87. It is provided to avoid any ambiguities and to provide an accurate record of the treatment of pending claims.

14. Claims 84, 86 and 87 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ohta et al. (U.S. Patent 5,294,790).

18. As per claims 86 and 87, Ohta et al. disclose a substrate comprising silicon and corresponding thin films (column 4, lines 28-29). Ohta et al. do not explicitly disclose an apparatus comprising patterned layers of silicon compounds, including silicon nitride.

19. It would have been obvious to modify the apparatus of Ohta et al. such that it comprised a silicon substrate and patterned layers of silicon compounds including silicon nitride. One would have been motivated to make such a modification so that the resulting substrate is provided with sufficient insulation to prevent the unwanted flow of charge on the supporting structure, while also providing mechanical strength for the mounting of optical components.

Examiner C. Thomas